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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	168
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f439bgt6

List of tables

2.1 Full compatibility throughout the family

The STM32F437xx and STM32F439xx devices are part of the STM32F4 family. They are fully pin-to-pin, software and feature compatible with the STM32F2xx devices, allowing the user to try different memory densities, peripherals, and performances (FPU, higher frequency) for a greater degree of freedom during the development cycle.

The STM32F437xx and STM32F439xx devices maintain a close compatibility with the whole STM32F10xx family. All functional pins are pin-to-pin compatible. The STM32F437xx and STM32F439xx, however, are not drop-in replacements for the STM32F10xx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xx to the STM32F43x family remains simple as only a few pins are impacted.

Figure 1, *Figure 2*, and *Figure 3*, give compatible board designs between the STM32F4xx, STM32F2xx, and STM32F10xx families.

Figure 1. Compatible board design STM32F10xx/STM32F2xx/STM32F4xx for LQFP100 package

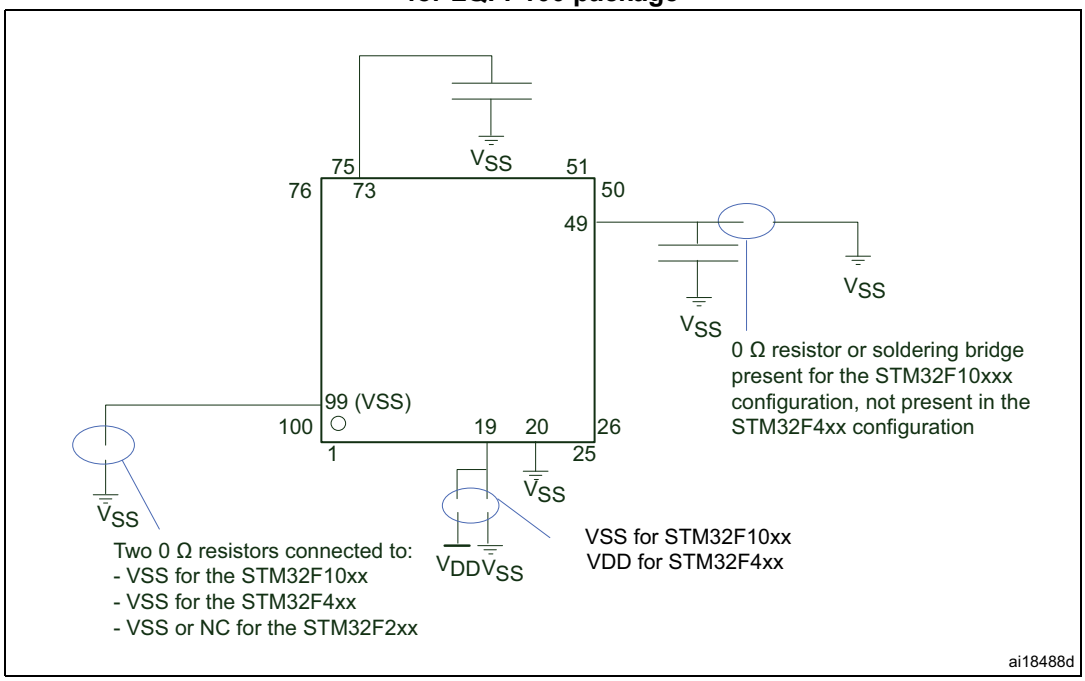
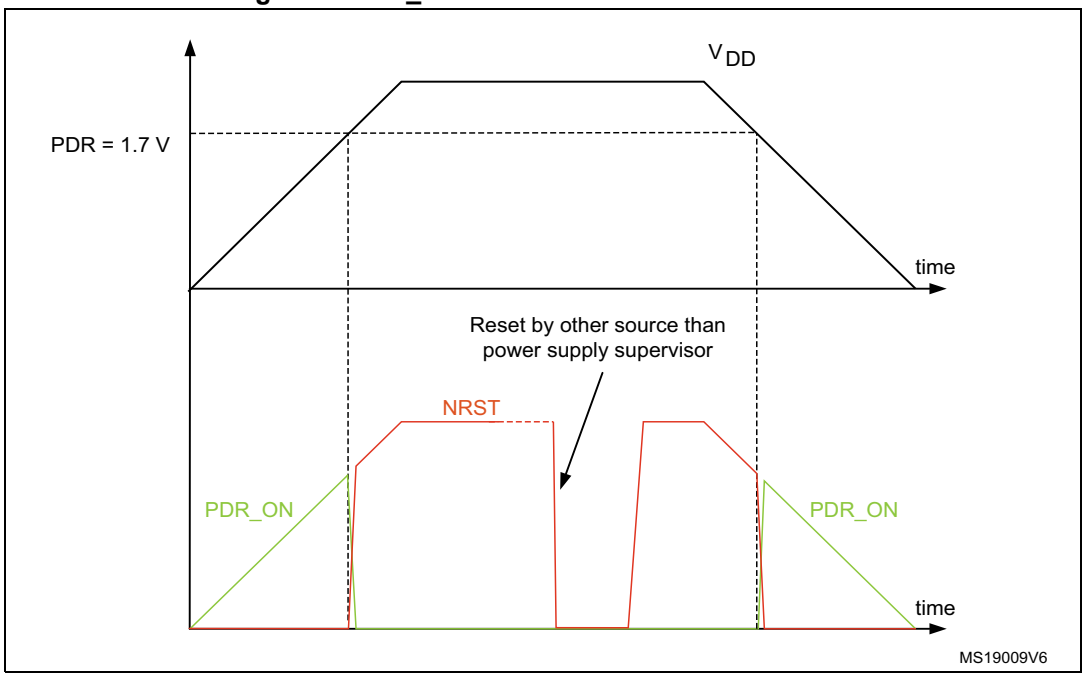


Figure 7. PDR_ON control with internal reset OFF



3.18 Voltage regulator

The regulator has four operating modes:

- Regulator ON
  - Main regulator mode (MR)
  - Low power regulator (LPR)
  - Power-down
- Regulator OFF

3.18.1 Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR mode used in Run/sleep modes or in Stop modes
  - In Run/Sleep mode

    The MR mode is used either in the normal mode (default mode) or the over-drive mode (enabled by software). Different voltages scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption.

3.35 Digital camera interface (DCMI)

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

3.36 Cryptographic acceleration

The devices embed a cryptographic accelerator. This cryptographic accelerator provides a set of hardware acceleration for the advanced cryptographic algorithms usually needed to provide confidentiality, authentication, data integrity and non repudiation when exchanging messages with a peer.

- These algorithms consists of:

  Encryption/Decryption

  – DES/TDES (data encryption standard/triple data encryption standard): ECB (electronic codebook) and CBC (cipher block chaining) chaining algorithms, 64-, 128- or 192-bit key

  – AES (advanced encryption standard): ECB, CBC, GCM, CCM, and CTR (counter mode) chaining algorithms, 128, 192 or 256-bit key

  Universal hash

  – SHA-1 and SHA-2 (secure hash algorithms)

  – MD5

  – HMAC

The cryptographic accelerator supports DMA request generation.

3.37 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

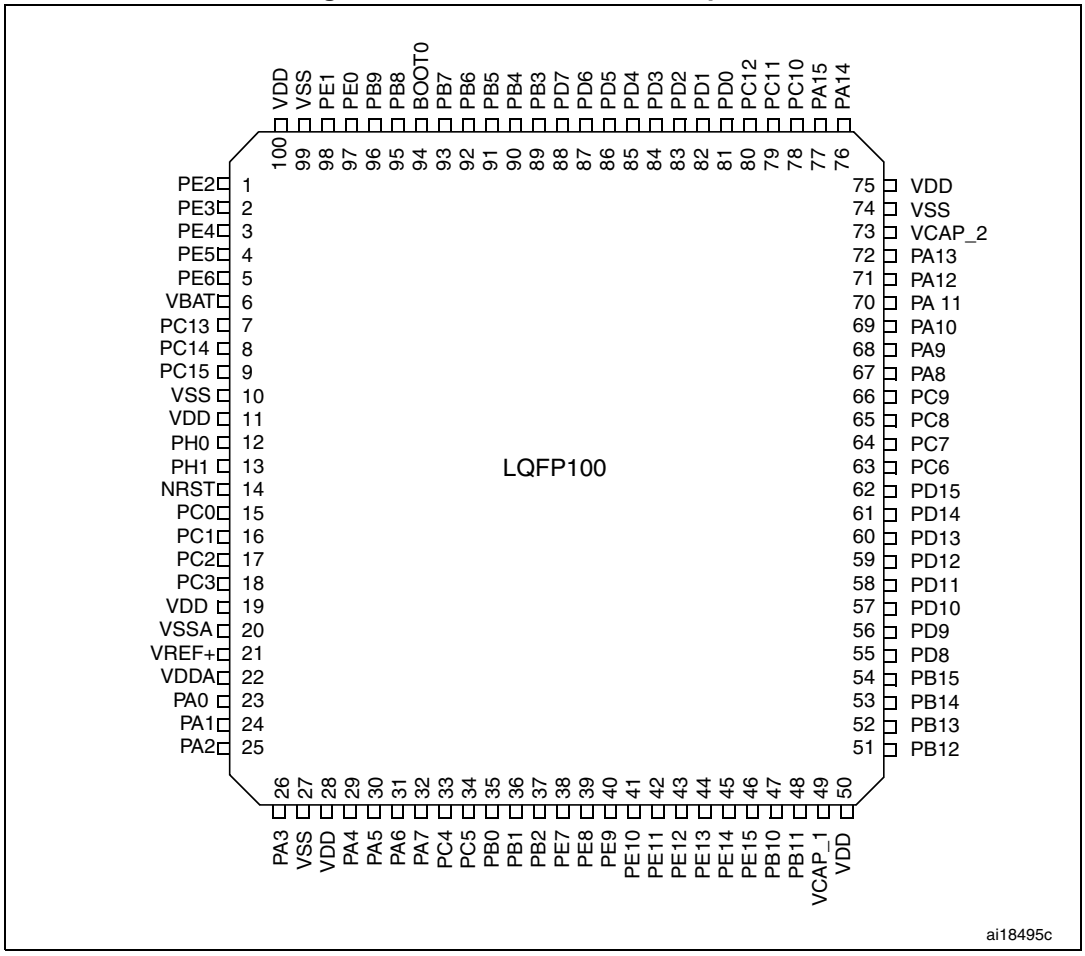
3.38 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

4 Pinouts and pin description

Figure 11. STM32F43x LQFP100 pinout



1. The above figure shows the package top view.

Table 10. STM32F437xx and STM32F439xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
82	115	C9	C12	143	C4	165	C12	PD1	I/O	FT	-	CAN1_TX, FMC_D3, EVENTOUT	-
83	116	B9	D12	144	A3	166	D12	PD2	I/O	FT	-	TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
84	117	A9	D11	145	B4	167	C11	PD3	I/O	FT	-	SPI2_SCK/I2S2_CK, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	-
85	118	D8	D10	146	B5	168	D11	PD4	I/O	FT	-	USART2_RTS, FMC_NOE, EVENTOUT	-
86	119	C8	C11	147	A4	169	C10	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	120	-	D8	148	-	170	F8	V_{SS}	S		-	-	-
-	121	D6	C8	149	C5	171	E9	V_{DD}	S		-	-	-
87	122	B8	B11	150	F4	172	B11	PD6	I/O	FT	-	SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	-
88	123	A8	A11	151	A5	173	A11	PD7	I/O	FT	-	USART2_CK, FMC_NE1/FMC_NCE2, EVENTOUT	-
-	-	-	-	-	-	174	B10	PJ12	I/O	FT	-	LCD_B0, EVENTOUT	-
-	-	-	-	-	-	175	B9	PJ13	I/O	FT	-	LCD_B1, EVENTOUT	-
-	-	-	-	-	-	176	C9	PJ14	I/O	FT	-	LCD_B2, EVENTOUT	-
-	-	-	-	-	-	177	D10	PJ15	I/O	FT	-	LCD_B3, EVENTOUT	-
-	124	NC (2)	C10	152	E5	178	D9	PG9	I/O	FT	-	USART6_RX, FMC_NE2/FMC_NCE3, DCMI_VSYNC(8), EVENTOUT	-

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 20. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

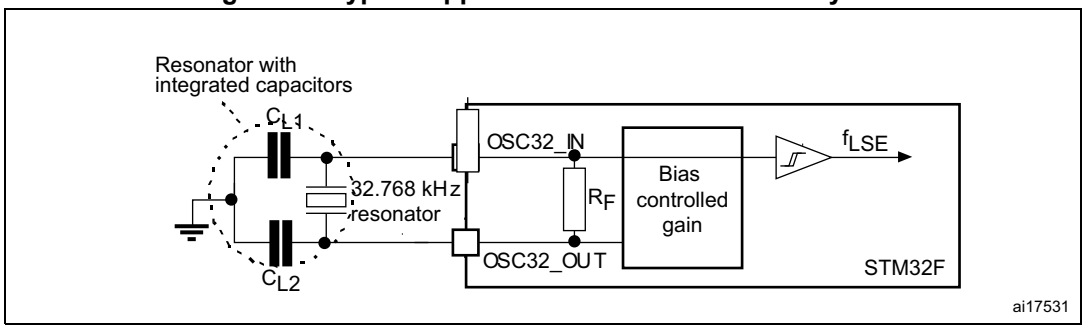
Subject to general operating conditions for T_A.

Table 21. Operating conditions at power-up / power-down (regulator OFF)(1)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Figure 30. Typical application with a 32.768 kHz crystal



6.3.10 Internal clock source characteristics

The parameters given in *Table 41* and *Table 42* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

High-speed internal (HSI) RC oscillator

Table 41. HSI oscillator characteristics (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user-trimming step (2)	-	-	-	1	%
	Accuracy of the HSI oscillator	T_A = –40 to 105 °C(3)	− 8	-	4.5	%
		T_A = –10 to 85 °C(3)	− 4	-	4	%
		T_A = 25 °C(4)	− 1	-	1	%
$t_{su(HSI)}$(2)	HSI oscillator startup time	-	-	2.2	4	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption	-	-	60	80	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design.
3. Guaranteed by characterization results.
4. Factory calibrated, parts not soldered.

6.3.17 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 56: I/O static characteristics* are derived from tests performed under the conditions summarized in *Table 17*. All I/Os are CMOS and TTL compliant.

Table 56. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	FT, TTa and NRST I/O input low level voltage	1.7 V≤V_{DD}≤3.6 V	-	-	$0.35V_{DD}$ − 0.04 (1)	V
					$0.3V_{DD}$ (2)	
	BOOT0 I/O input low level voltage	1.75 V≤V_{DD} ≤3.6 V, – 40 °C≤T_A ≤105 °C	-	-	$0.1V_{DD}$+0.1 (1)	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C	-	-		
V_{IH}	FT, TTa and NRST I/O input high level voltage (5)	1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}$+0.3 (1)	-	-	V
			$0.7V_{DD}$ (2)			
	BOOT0 I/O input high level voltage	1.75 V≤V_{DD} ≤3.6 V, – 40 °C≤T_A ≤105 °C	$0.17V_{DD}$+0.7 (1)	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
V_{HYS}	FT, TTa and NRST I/O input hysteresis	1.7 V≤V_{DD}≤3.6 V	10%V_{DD} (3)	-	-	V
	BOOT0 I/O input hysteresis	1.75 V≤V_{DD} ≤3.6 V, – 40 °C≤T_A ≤105 °C	0.1	-	-	
		1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
I_{lkg}	I/O input leakage current (4)	V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT input leakage current (5)	V_{IN} = 5 V	-	-	3	

Ethernet characteristics

Unless otherwise specified, the parameters given in *Table 71*, *Table 72* and *Table 73* for SMI, RMII and MII are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in *Table 17* with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF for 2.7 V < V_{DD} < 3.6 V
- Capacitive load C = 20 pF for 1.71 V < V_{DD} < 3.6 V
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output characteristics.

Table 71 gives the list of Ethernet MAC signals for the SMI (station management interface) and *Figure 47* shows the corresponding timing diagram.

Figure 47. Ethernet SMI timing diagram

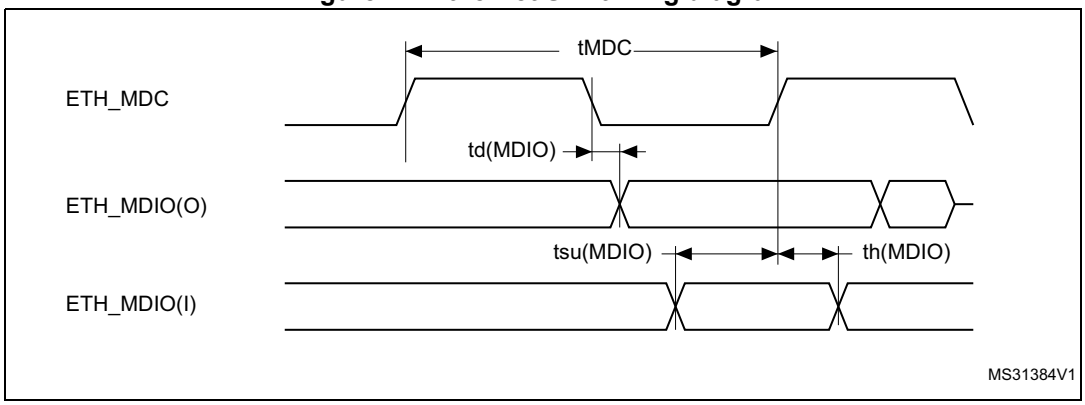


Table 71. Dynamics characteristics: Ethernet MAC signals for SMI(1)

Symbol	Parameter	Min	Typ	Max	Unit
t_{MDC}	MDC cycle time(2.38 MHz)	411	420	425	ns
$T_{d(MDIO)}$	Write data valid time	6	10	13	
$t_{su(MDIO)}$	Read data setup time	12	-	-	
$t_{h(MDIO)}$	Read data hold time	0	-	-	

1. Guaranteed by characterization results.

Table 90. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK} - 1$	$3T_{HCLK}+0.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK} - 0.5$	$2T_{HCLK}$	ns
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK} - 1$	$T_{HCLK}+1$	ns
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	1	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	2	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+0.5$	ns
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	0	-	ns
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK} - 0.5$	-	ns
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}+1.5$	-	ns
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}+1$	-	ns
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 91. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1$	$5T_{HCLK}+1.5$	ns
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	ns
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$		ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 93. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$9T_{HCLK}$	$9T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$7T_{HCLK}$	$7T_{HCLK}+2$	ns
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}+1.5$	-	ns
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}-1$	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Synchronous waveforms and timings

Figure 59 through *Figure 62* represent synchronous waveforms and *Table 94* through *Table 97* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F4xx reference manual : RM0090)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the T_{HCLK} is the HCLK clock period (with maximum FMC_CLK = 90 MHz).

6.3.28 LCD-TFT controller (LTDC) characteristics

Unless otherwise specified, the parameters given in *Table 107* for LCD-TFT are derived from tests performed under the ambient temperature, f_{HCLK} frequency and VDD supply voltage summarized in *Table 17*, with the following configuration:

- LCD_CLK polarity: high
- LCD_DE polarity : low
- LCD_VSYNC and LCD_HSYNC polarity: high
- Pixel formats: 24 bits

Table 107. LTDC characteristics

Symbol	Parameter	Min	Max	Unit
f_{CLK}	LTDC clock output frequency	-	42	MHz
D_{CLK}	LTDC clock output duty cycle	45	55	%
$t_{w(CLKH)}$ $t_{w(CLKL)}$	Clock High time, low time	tw(CLK)/2 − 0.5	tw(CLK)/2+0.5	ns
$t_{v(DATA)}$	Data output valid time	-	3.5	
$t_{h(DATA)}$	Data output hold time	1.5	-	
$t_{v(HSYNC)}$	HSYNC/VSYNC/DE output valid time	-	2.5	
$t_{v(VSYNC)}$				
$t_{v(DE)}$				
$t_{h(HSYNC)}$	HSYNC/VSYNC/DE output hold time	2	-	
$t_{h(VSYNC)}$				
th(DE)				

6.3.29 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 108* for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output characteristics.

Figure 78. SDIO high-speed mode

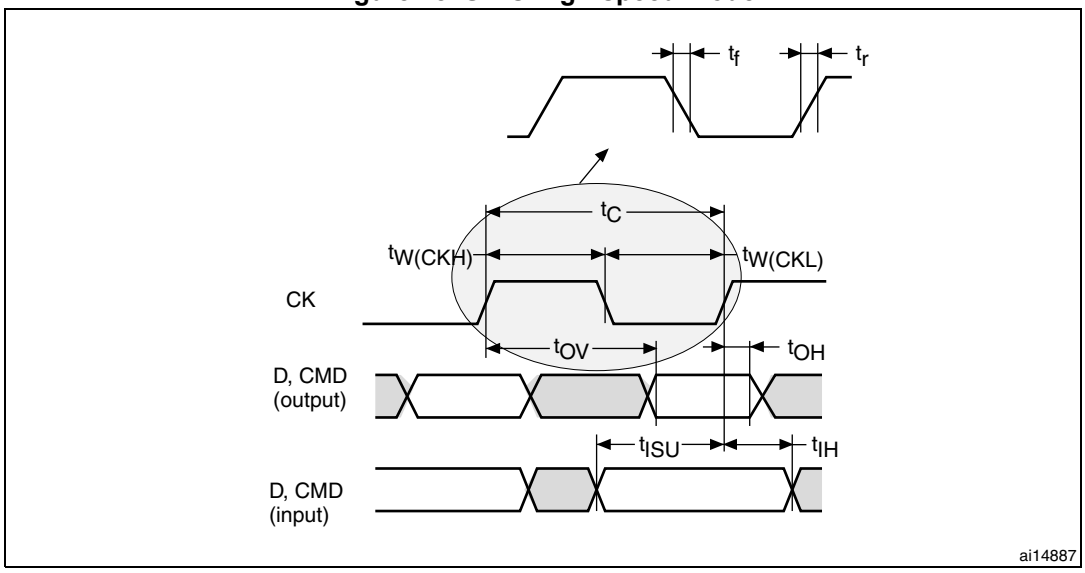
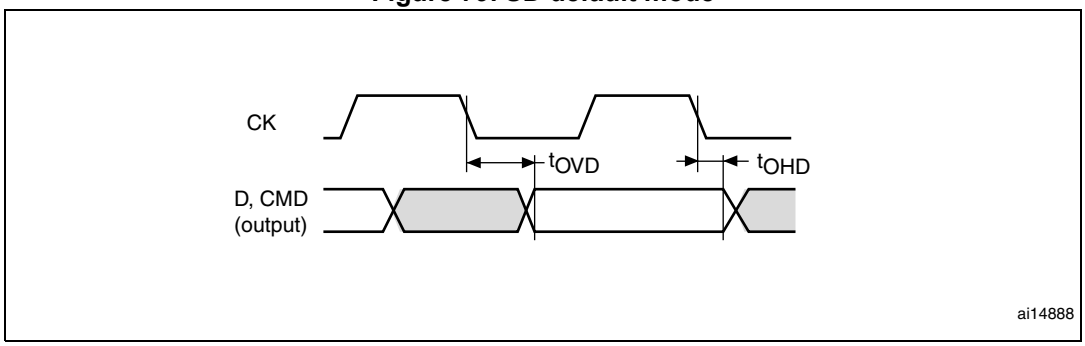
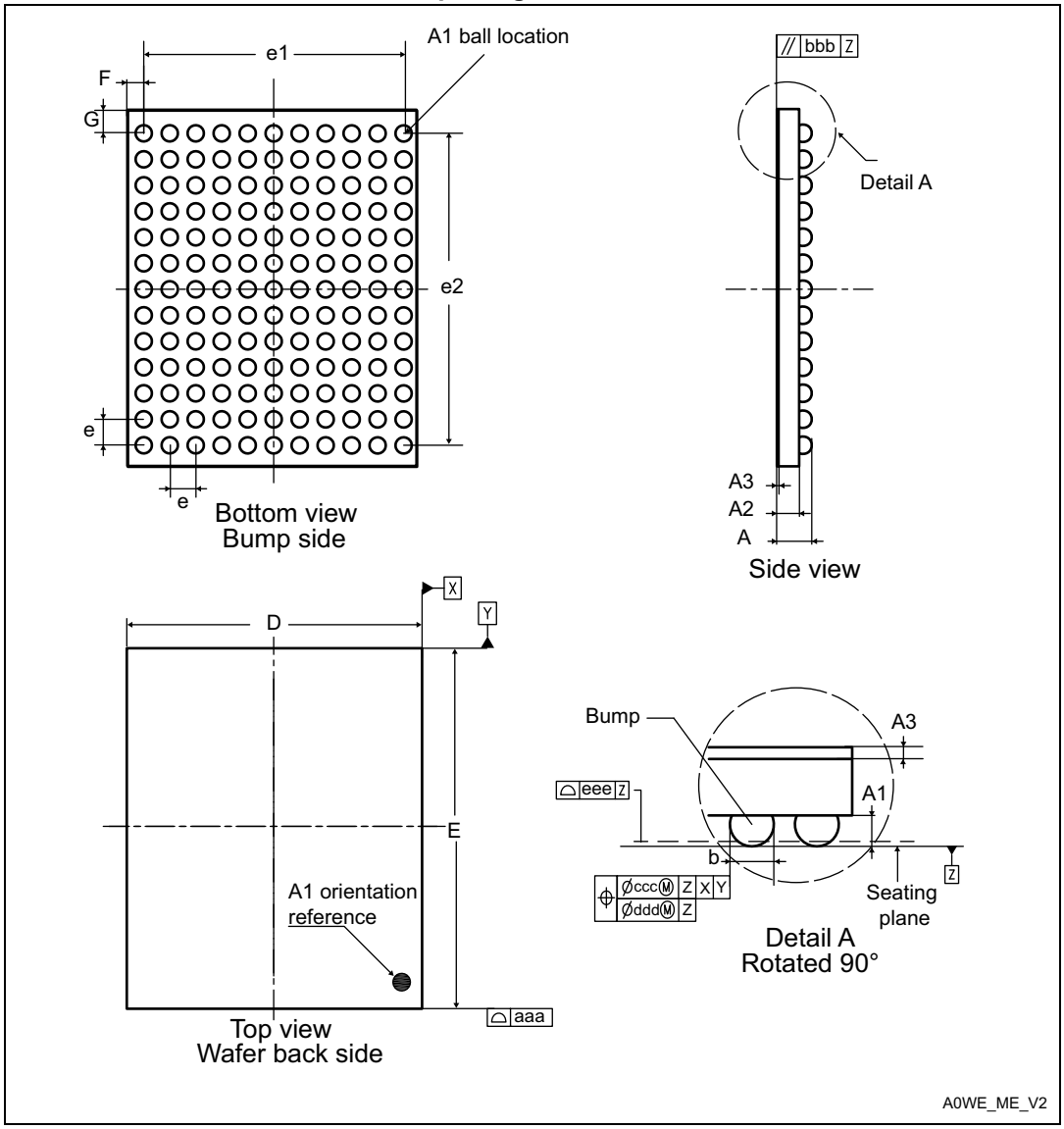


Figure 79. SD default mode



7.2 WLCSP143 package information

Figure 83. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

Table 111. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	0.155	0.175	0.195	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	4.486	4.521	4.556	0.1766	0.1780	0.1794
E	5.512	5.547	5.582	0.2170	0.2184	0.2198
e	-	0.400	-	-	0.0157	-
e1	-	4.000	-	-	0.1575	-
e2	-	4.800	-	-	0.1890	-
F	-	0.2605	-	-	0.0103	-
G	-	0.3735	-	-	0.0147	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 84. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale recommended footprint

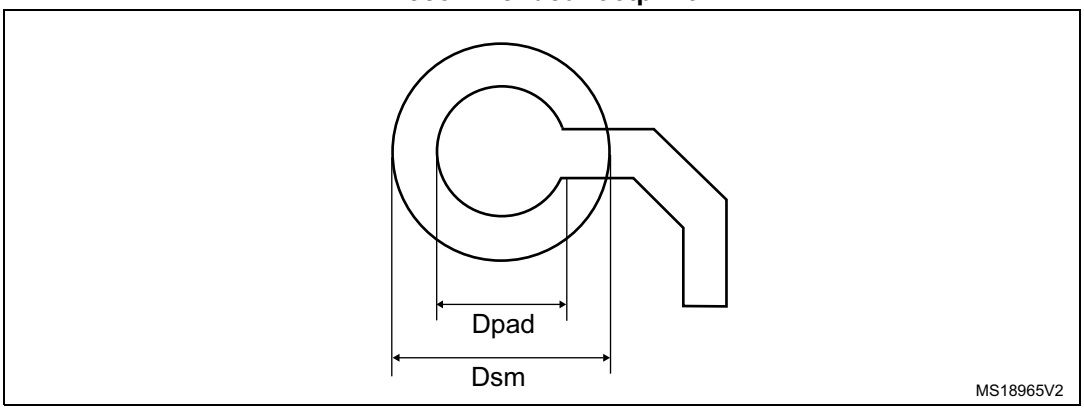


Table 114. LQFP176 - 176-pin, 24 x 24 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
ZD	-	1.250	-	-	0.0492	-
E	23.900	-	24.100	0.9409	-	0.9488
HE	25.900	-	26.100	1.0197	-	1.0276
ZE	-	1.250	-	-	0.0492	-
e	-	0.500	-	-	0.0197	-
L[2]	0.450	-	0.750	0.0177	-	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	-	7°	0°	-	7°
ccc	-	-	0.080	-	-	0.0031

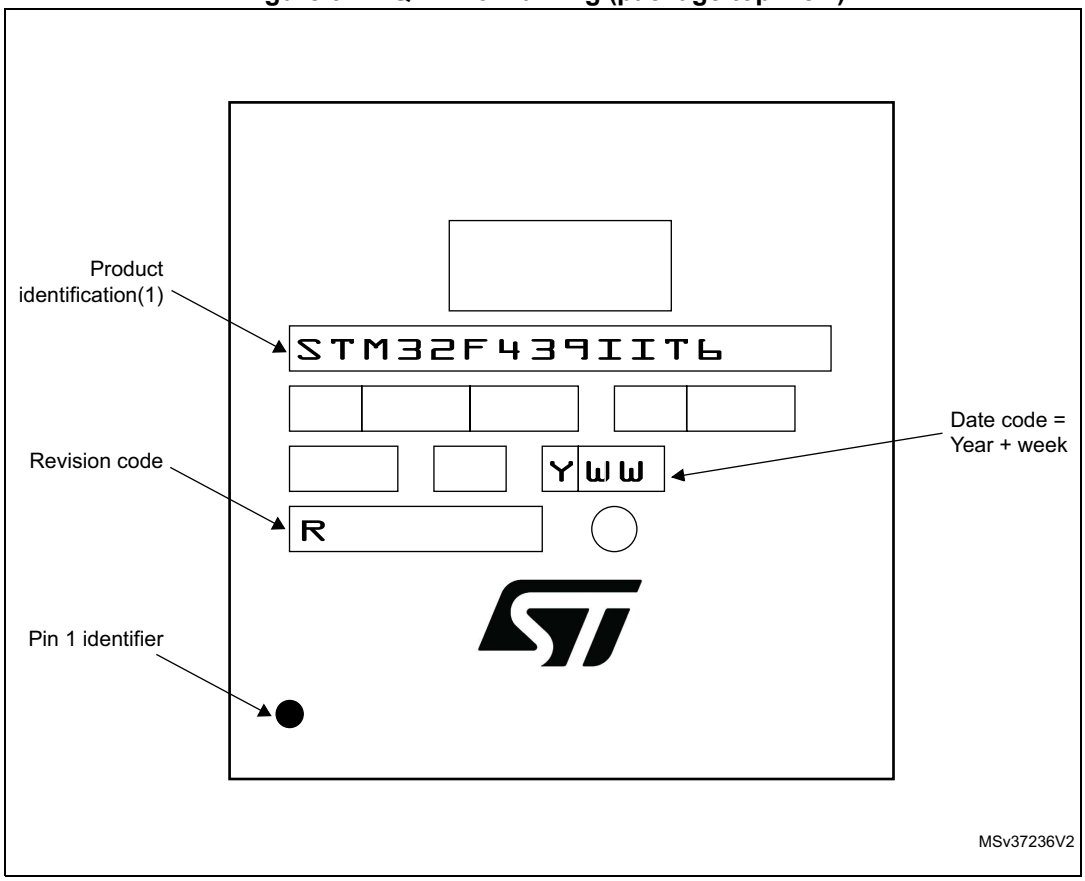
1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. L dimension is measured at gauge plane at 0.25 mm above the seating plane.

Device marking for LQFP176

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 91. LQFP176 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 124. Document revision history (continued)

Date	Revision	Changes
24-Apr-2014	5	Changed SVGA (800x600) into XGA1024x768) on cover page and in *Section 3.10: LCD-TFT controller (available only on STM32F439xx)*. Added DCMI_VSYNC alternate function on PG9 and updated note *6.* in *Table 10: STM32F437xx and STM32F439xx pin and ball definitions* and *Table 12: STM32F437xx and STM32F439xx alternate function mapping*. Added note *2.*below*Figure 16: STM32F43x UFBGA169 ballout*. Updated *Section 3.18.2: Regulator OFF*. Updated signal corresponding to pin L5 in *Figure 12: STM32F43x WLCSP143 ballout*. Updated *Table 53: ESD absolute maximum ratings*. Updated V_{IH} in *Table 56: I/O static characteristics*. Added condition V_{DD}>1.7 V in *Table 58: I/O AC characteristics*. Removed notes 3 and 4 in *Table 62: SPI dynamic characteristics*. Added ACC_{HSE} in *Table 39: HSE 4-26 MHz oscillator characteristics* and ACC_{LSE} in *Table 40: LSE oscillator characteristics (fLSE = 32.768 kHz)*. Removed note 3 in *Table 80: Temperature sensor characteristics*. Added *Figure 82: LQFP100 marking example (package top view)*, *Figure 85: WLCSP143 marking example (package top view)*, *Figure 88: LQFP144 marking example (package top view)*, *Figure 91: LQFP176 marking (package top view)*, *Figure 94: LQFP208 marking example (package top view)*, *Figure 97: UFBGA169 marking example (package top view)* and *Figure 100: UFBGA176+25 marking example (package top view)*. Added *Appendix A: Recommendations when using internal reset OFF* and removed Internal reset OFF hardware connection appendix.